

N-Channel 20-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical	Appl	icatio	ns:
<i>3</i> I			

- Power Routing
- Li Ion Battery Packs
- Level Shifting and Driver Circuits

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
20	58 @ V _{GS} = 4.5V	3.9	
	82 @ V _{GS} = 2.5V	3.3	







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current ^a	T _A =25°C	I _D	3.9	
Continuous Drain Current	T _A =70°C	' D	3.1	Α
Pulsed Drain Current ^b		I_{DM}	15	
Continuous Source Current (Diode Conduction) a			2	Α
Power Dissipation ^a	T _A =25°C	P_{D}	1.3	W
Power Dissipation	T _A =70°C	י ט	0.8	VV
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	100	°C/W	
IMAXIIIIUIII JUIICUOII-to-Alfibierit	Steady State	Ţ '`θJA	166	C/VV	

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

MI2332N

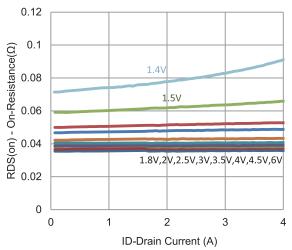
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	0.4			V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA
Zana Cata Valtana Busin Comment		$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	6			Α
Drain Course On Besistance a	r	$V_{GS} = 4.5 \text{ V}, I_D = 2.6 \text{ A}$			58	mΩ
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 2.1 \text{ A}$			82	11122
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 2.6 \text{ A}$		4		S
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 1 \text{ A}, V_{GS} = 0 \text{ V}$		0.65		V
		Dynamic ^b				
Total Gate Charge	Q_g	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_{D} = 2.6 \text{ A}$		12		
Gate-Source Charge	Q_{gs}			2.0		nC
Gate-Drain Charge	Q_{gd}	ID - 2.0 A		2.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 10 \text{ V}, R_{L} = 3.9 \Omega,$ $I_{D} = 2.6 \text{ A},$ $V_{GEN} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$		8		
Rise Time	t _r			33		ne
Turn-Off Delay Time	$t_{d(off)}$			59		ns
Fall Time	t _f			18		
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 Mhz		720		
Output Capacitance	C _{oss}			74		рF
Reverse Transfer Capacitance	C _{rss}			69		

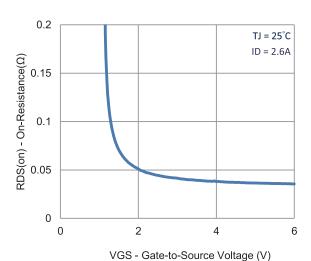
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

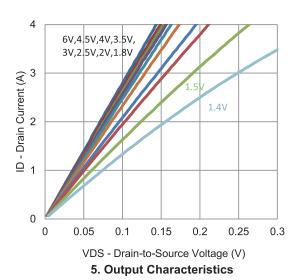
Typical Electrical Characteristics

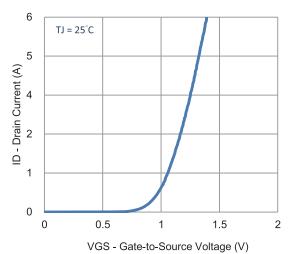


1. On-Resistance vs. Drain Current

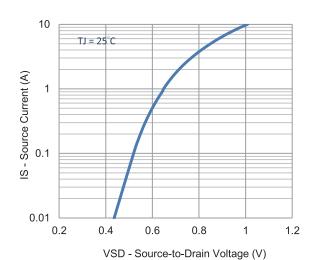


3. On-Resistance vs. Gate-to-Source Voltage

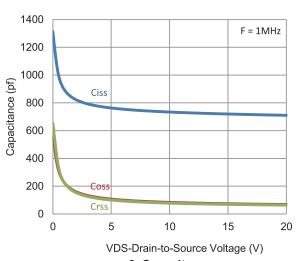




2. Transfer Characteristics

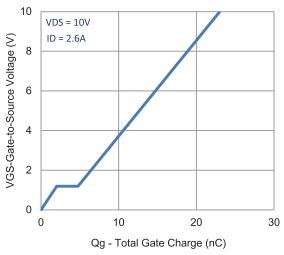


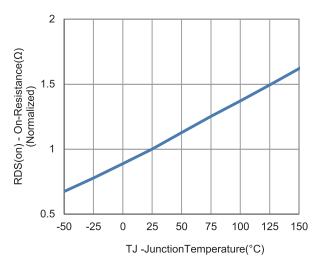
4. Drain-to-Source Forward Voltage



6. Capacitance

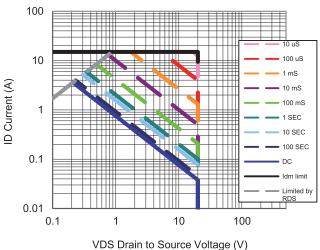


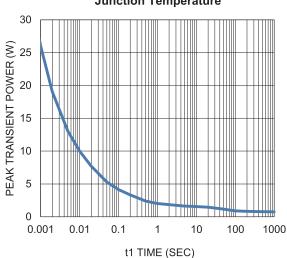




7. Gate Charge

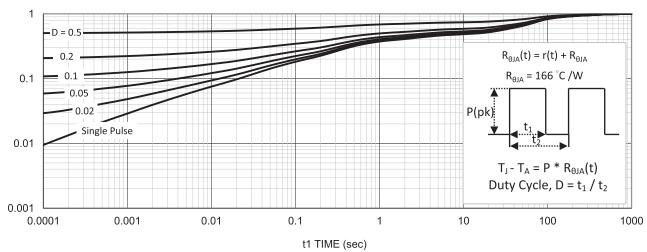






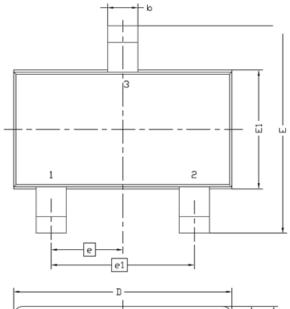
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation

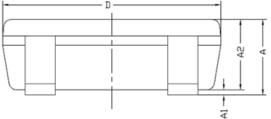


11. Normalized Thermal Transient Junction to Ambient

Package Information

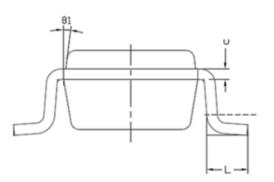


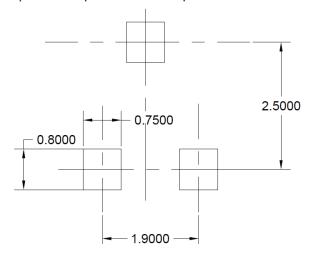
Symbol	MILLIMETERS		
Syllibol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
Е	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		



Recommended Pad Layout

Note: Drain opening is recommended to be solder mask defined in a copper fill to provide improved thermal performance





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